SHANGHAI SUNRISE ELECTRONICS CO., LTD.

1N4001G THRU 1N4007G GLASS PASSIVATED

JUNCTION RECTIFIER

TECHNICAL SPECIFICATION

VOLTAGE: 50 TO 1000V CURRENT: 1.0A

FEATURES

- Molded case feature for auto insertion
- Glass passivated chip
- High current capability
- Low leakage current
- High surge capability
- High temperature soldering guaranteed: 250°C/10sec/0.375"(9.5mm) lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode
- Mounting position: Any

1.0 (25.4) .034 (0.9) DIA. 1.0 (25.4) .028 (0.7) DIA. .106 (4.2) .107 (2.7) DIA. 1.0 (25.4) .080 (2.0) DIA. 1.0 (25.4) .080 (2.0) DIA. Dimensions in inches and (millimeters)

DO - 41

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

| RATINGS | SYMBOL | 1N40 01G | 1N40 02G | 1N40 03G | 1N40 04G | 1N40 05G | 1N40 06G | 1N40 07G | UNITS |
|--|-------------------------|-------------|-------------|-------------|-------------|-------------|-------------|-------------|----------|
| Maximum Repetitive Peak Reverse Voltage | V _{RRM} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS Voltage | V _{RMS} | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Maximum DC Blocking Voltage | V _{DC} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum Average Forward Rectified Current (9.5mm lead length, at $T_a=75^{\circ}C$) | I _{F(AV)} | 1.0 | | | | | | | А |
| Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load) | I _{FSM} | 30.0 | | | | | | | А |
| Maximum Instantaneous Forward Voltage (at rated forward current) | V _F | 1.1 | | | | | V | | |
| Maximum DC Reverse Current $T_a=25^{\circ}C$ (at rated DC blocking voltage) $T_a=100^{\circ}C$ | D | 5.0 50 | | | | | | | μΑ μΑ |
| Typical Junction Capacitance (Note 1) | CJ | 15.0 | | | | | | | pF |
| Typical Thermal Resistance (Note 2) | R _θ (ja) | 50.0 | | | | | | | °C/W |
| Storage and Operation Junction Temperature | T_{STG},T_{J} | -65 to +150 | | | | | | °C | |
| Note: 1.Measured at 1.0 MHz and applied voltage | e of 4.0V _{dc} | | | | | | | | |

2.Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C. board mounted

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